

ESD56191N

1-Line, Bi-directional, Transient Voltage Suppressor

<http://www.sh-willsemi.com>

Descriptions

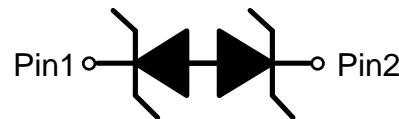
The ESD56191N is a TVS (Transient Voltage Suppressor) designed to protect sensitive electronic components which are connected to data and power lines from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and lightning.



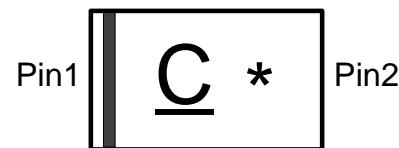
DFN1006-2L

The ESD56191N may be used to provide ESD protection up to $\pm 30\text{kV}$ (contact discharge) according to IEC61000-4-2, and withstand peak pulse current up to 28A (8/20 μs) according to IEC61000-4-5.

The ESD56191N is available in DFN1006-2L package. Standard products are Pb-free and Halogen-free.



Circuit diagram



C = Device code
* = Month code (A~Z)

Marking (Top View)

Features

- Reverse stand-off voltage: $\pm 4.8\text{V}$ Max.
- Transient protection for each line according to IEC61000-4-2 (ESD): $\pm 30\text{kV}$ (contact discharge)
IEC61000-4-5 (surge): 28A (8/20 μs)
- Capacitance: $C_J = 60\text{pF}$ typ.
- Low clamping voltage
- Low leakage current
- Solid-state silicon technology

Applications

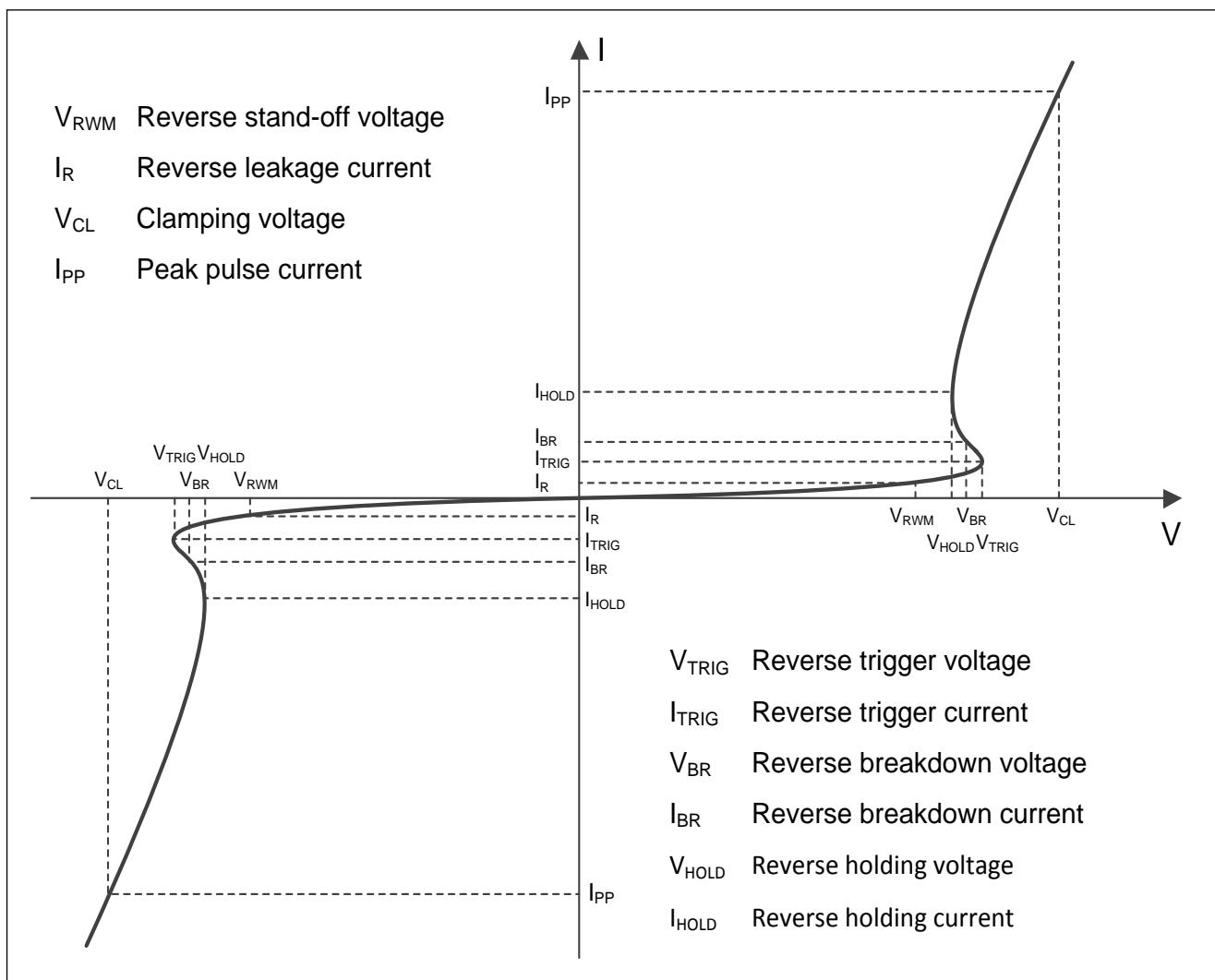
- Computers and peripherals
- Cellular handsets
- Portable Electronics
- Notebooks
- Camera

Order information

Device	Package	Shipping
ESD56191N-2/TR	DFN1006-2L	10000/Tape&Reel

Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu s$)	P_{pk}	420	W
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	28	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 30	kV
ESD according to IEC61000-4-2 contact discharge		± 30	
Junction temperature	T_J	125	$^{\circ}C$
Operating temperature	T_{OP}	-40~85	$^{\circ}C$
Lead temperature	T_L	260	$^{\circ}C$
Storage temperature	T_{STG}	-55~150	$^{\circ}C$

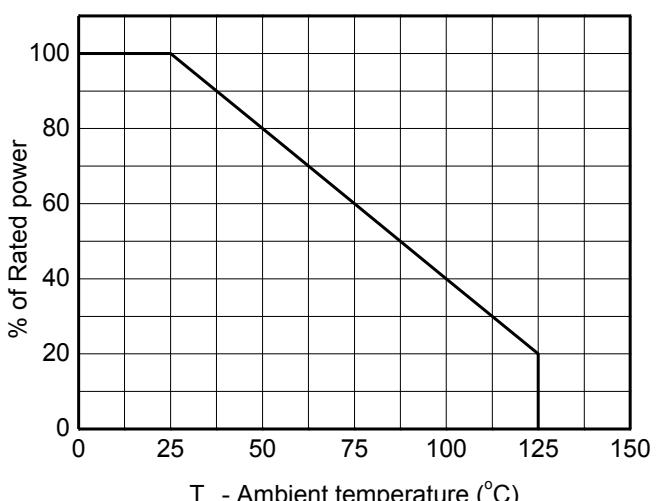
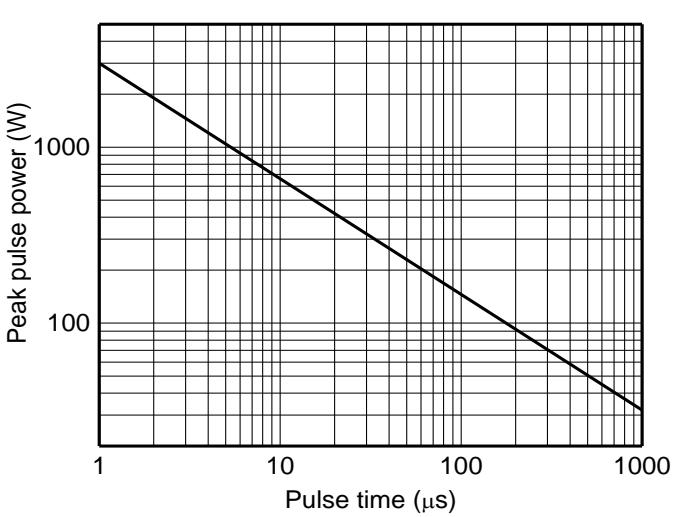
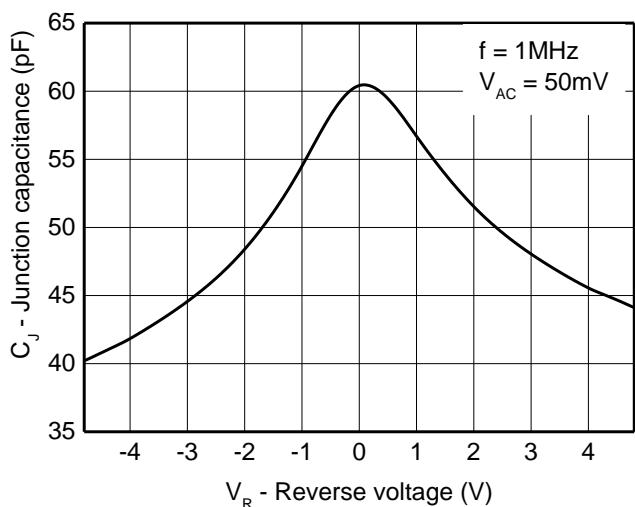
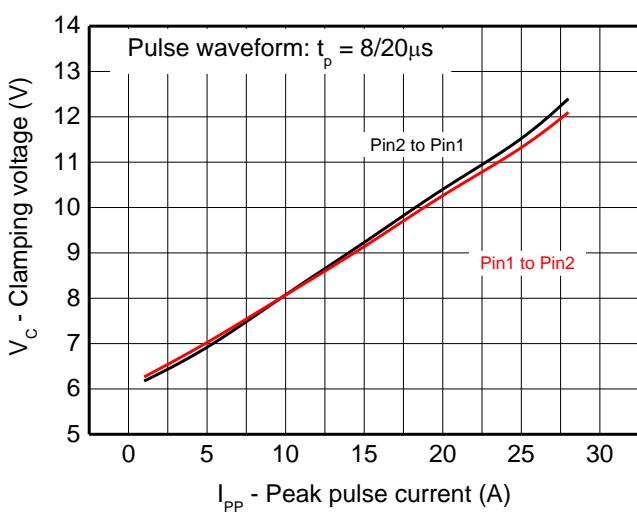
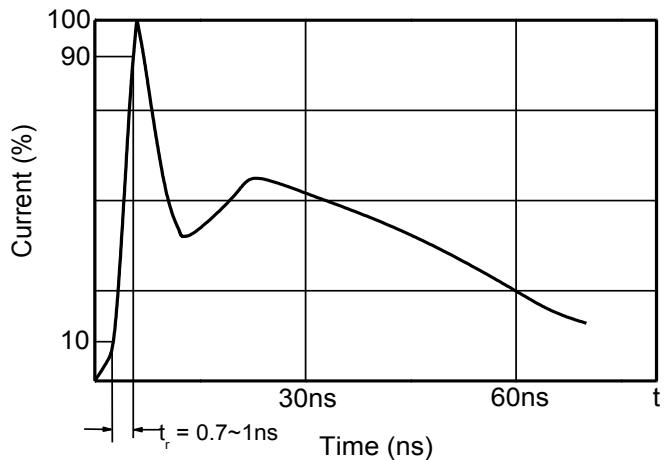
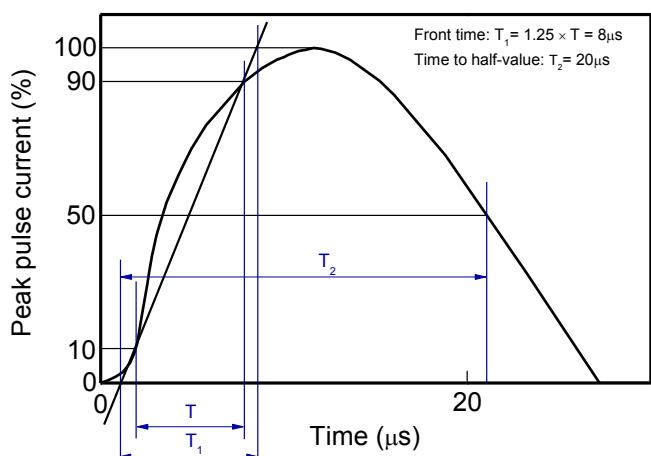
Electrical characteristics ($T_A=25^{\circ}C$, unless otherwise noted)

Definitions of electrical characteristics

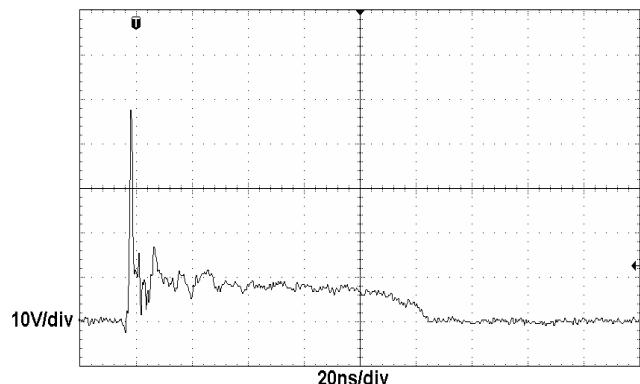
Electrical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				± 4.8	V
Reverse leakage current	I_R	$V_{RWM} = 4.8V$		<1	100	nA
Reverse breakdown voltage	V_{BR}	$I_{BR} = 1\text{mA}$	5.1			V
Reverse holding voltage	V_{HOLD}	$I_{HOLD} = 50\text{mA}$	5.1			V
Clamping voltage ¹⁾	V_{CL}	$I_{PP} = 16\text{A}, t_p = 100\text{ns}$		7		V
Clamping voltage ²⁾	V_{CL}	$V_{ESD} = 8\text{kV}$		8		V
Clamping voltage ³⁾	V_{CL}	$I_{PP} = 1\text{A}, t_p = 8/20\mu\text{s}$			9	V
		$I_{PP} = 5\text{A}, t_p = 8/20\mu\text{s}$			10	V
		$I_{PP} = 28\text{A}, t_p = 8/20\mu\text{s}$			15	V
Dynamic resistance ¹⁾	R_{DYN}	$t_p = 100\text{ns}$		0.04		Ω
Junction capacitance	C_J	$V_R = 0\text{V}, f = 1\text{MHz}$		60	75	pF
		$V_R = 4.8\text{V}, f = 1\text{MHz}$		40	50	pF

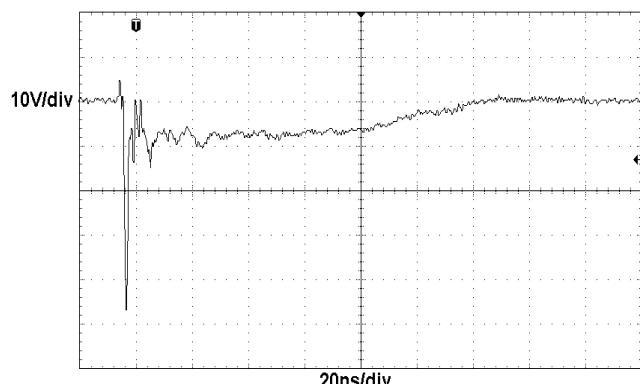
Notes:

- 1) TLP parameter: $Z_0 = 50\Omega$, $t_p = 100\text{ns}$, $t_r = 2\text{ns}$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

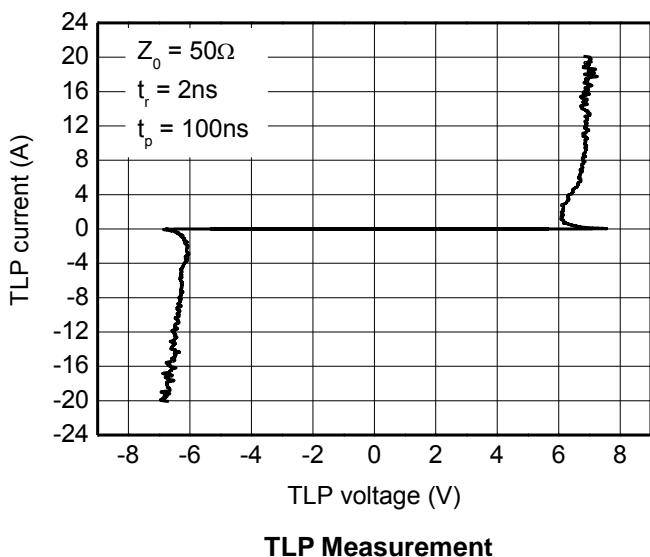
Typical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)


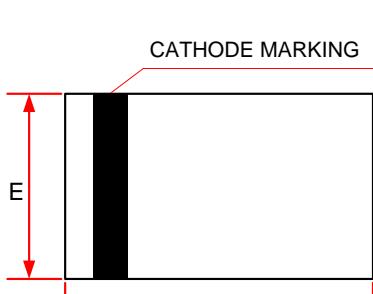
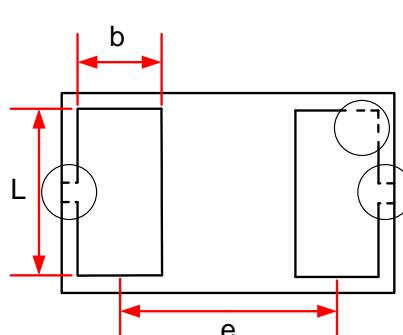
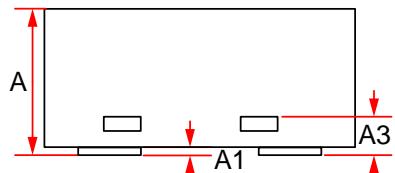
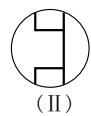
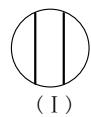
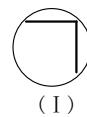
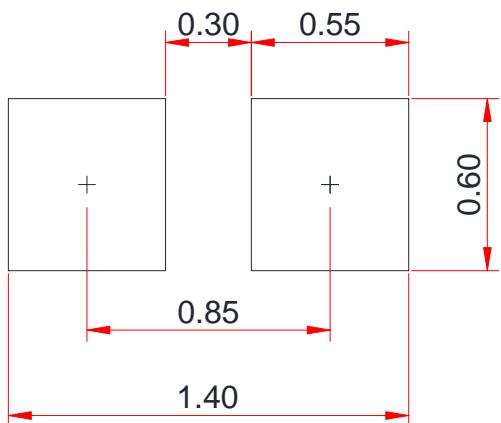
Typical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)


ESD clamping
(+8kV contact discharge per IEC61000-4-2)



ESD clamping
(-8kV contact discharge per IEC61000-4-2)



Package outline dimensions
DFN1006-2L

Top View

Bottom View

Side View
Recommend land pattern (Unit: mm)


Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.30	-	0.50
A1	0.00	-	0.05
A3	0.125 REF.		
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.20	0.25	0.30
L	0.45	0.50	0.55
e	0.65 Typ.		

Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.